

POWER MOSFET SURFACE MOUNT(SMD-1)

Product Summary

Part Number	RDS(on)	Id
IRFN9140	0.20Ω	-18A

HEXFET[®] MOSFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance. HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain capacitance.

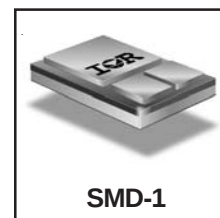
Absolute Maximum Ratings

	Parameter		Units
I_D @ $V_{GS} = -10V, T_C = 25^\circ C$	Continuous Drain Current	-18	A
I_D @ $V_{GS} = -10V, T_C = 100^\circ C$	Continuous Drain Current	-11	
I_{DM}	Pulsed Drain Current ①	-72	
P_D @ $T_C = 25^\circ C$	Max. Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	-18	A
E_{AR}	Repetitive Avalanche Energy ①	12.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction	-55 to 150	°C
T_{STG}	Storage Temperature Range		
	Package Mounting Surface Temperature	300 (for 5 S)	
	Weight	2.6(typical)	g

For footnotes refer to the last page

www.irf.com

IRFN9140
JANTX2N7236U
JANTXV2N7236U
JANS2N7236U
REF:MIL-PRF-19500/595
100V, P-CHANNEL
HEXFET[®] MOSFET TECHNOLOGY



SMD-1

Features:

- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Electrically Isolated
- Surface Mount
- Dynamic dv/dt Rating
- Light-weight

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
B _V D _{SS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -1.0mA
ΔB _V D _{SS} /ΔT _j	Temperature Coefficient of Breakdown Voltage	—	-0.087	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.20	Ω	V _{GS} = -10V, I _D = -11A④
		—	—	0.22		V _{GS} = -10V, I _D = -18A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	6.2	—	—	S (r _S)	V _{DS} > -15V, I _{DS} = -11A④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25	μA	V _{DS} = -80V, V _{GS} = 0V
		—	—	-250		V _{DS} = -80V V _{GS} = 0V, T _j = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = 20V
Q _g	Total Gate Charge	—	—	60	nC	V _{GS} = -10V, I _D = -18A V _{DS} = -50V
Q _{gs}	Gate-to-Source Charge	—	—	13		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	35.2		
t _{d(on)}	Turn-On Delay Time	—	—	35	ns	V _{DD} = -50V, I _D = -18A R _G = 9.1Ω, V _{GS} = -10V
t _r	Rise Time	—	—	85		
t _{d(off)}	Turn-Off Delay Time	—	—	85		
t _f	Fall Time	—	—	65		
L _S + L _D	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1400	—	pF	V _{GS} = 0V, V _{DS} = -25V f = 1.0MHz
C _{oss}	Output Capacitance	—	600	—		
C _{rss}	Reverse Transfer Capacitance	—	200	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-18	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-72		
V _{SD}	Diode Forward Voltage	—	—	-5.0	V	T _j = 25°C, I _S = -18A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	280	nS	T _j = 25°C, I _F = -18A, di/dt ≤ -100A/μs V _{DD} ≤ -30V ④
Q _{RR}	Reverse Recovery Charge	—	—	3.6	μc	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction to Case	—	—	1.0	°C/W	
R _{thJ-PCB}	Junction to PC Board	—	4.0	—		Soldered to a copper-clad PC board

Note: Corresponding Spice and Saber models are available on International Rectifier Website.

For footnotes refer to the last page

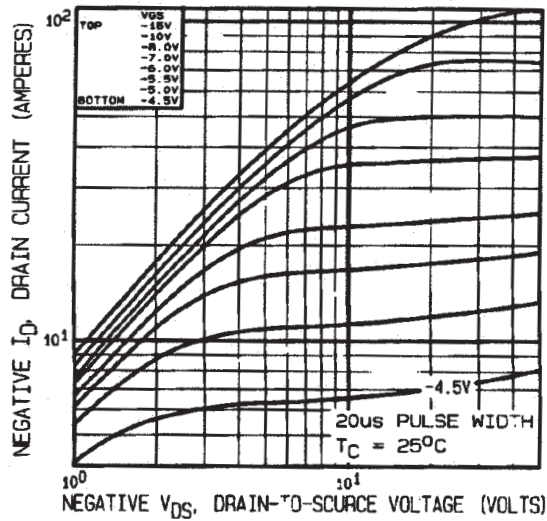


Fig 1. Typical Output Characteristics

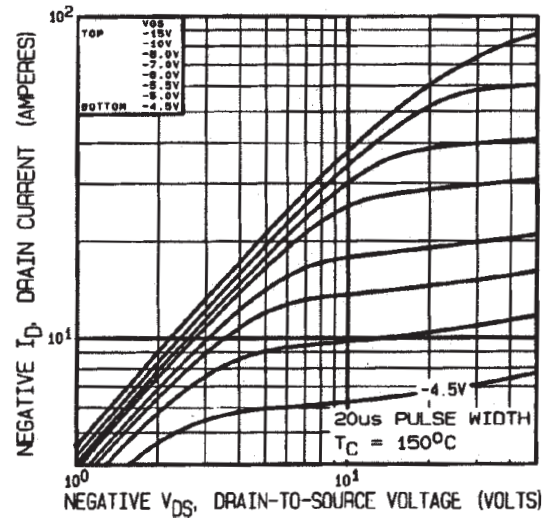


Fig 2. Typical Output Characteristics

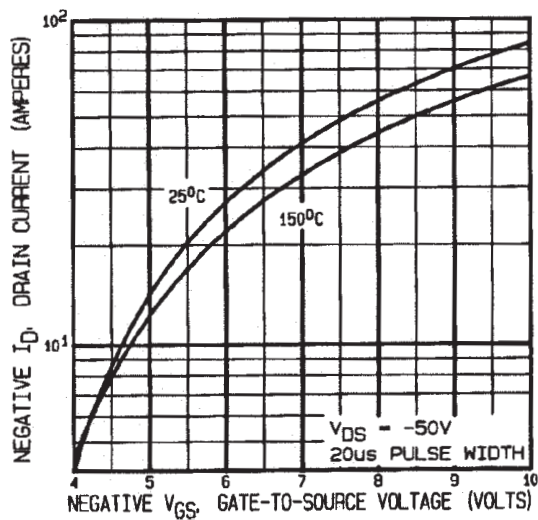


Fig 3. Typical Transfer Characteristics

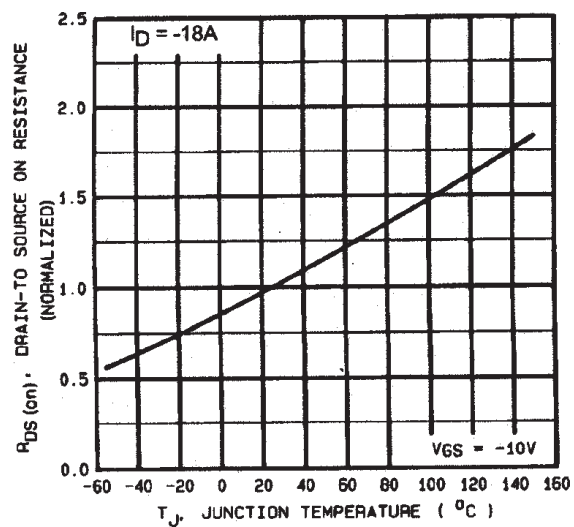


Fig 4. Normalized On-Resistance
Vs. Temperature

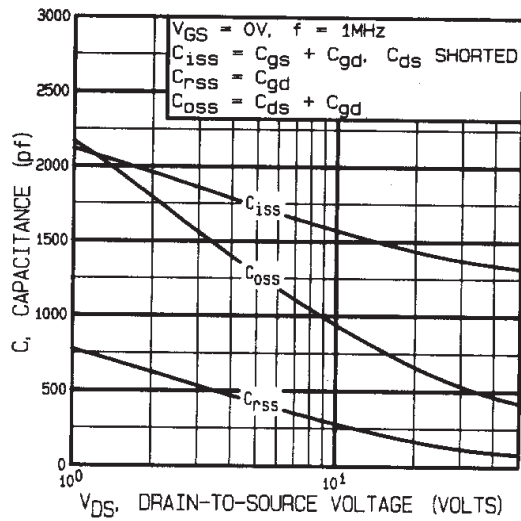


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

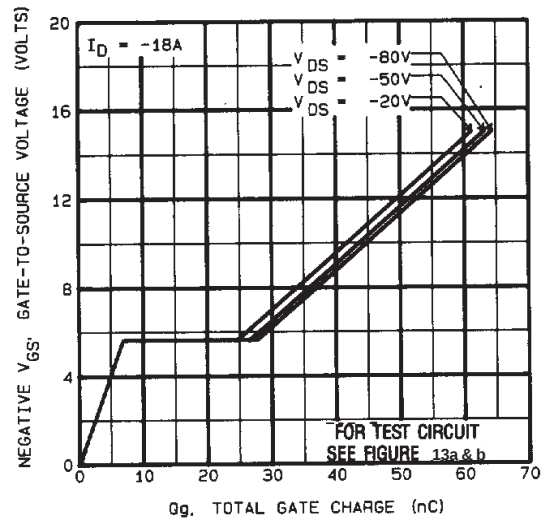


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

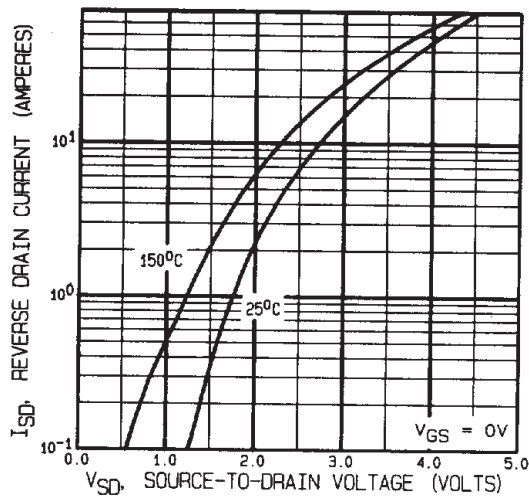


Fig 7. Typical Source-Drain Diode Forward Voltage

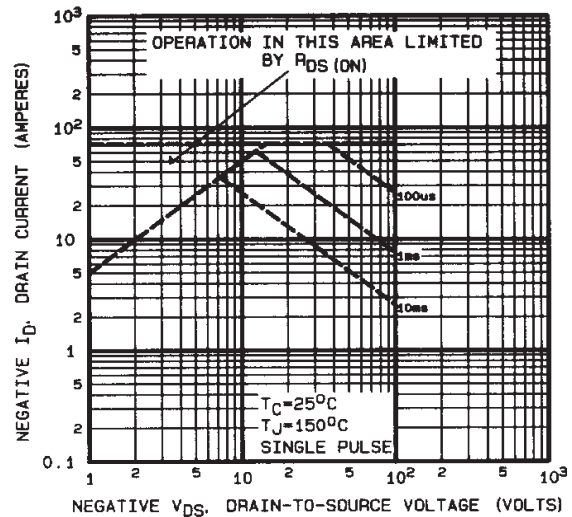


Fig 8. Maximum Safe Operating Area

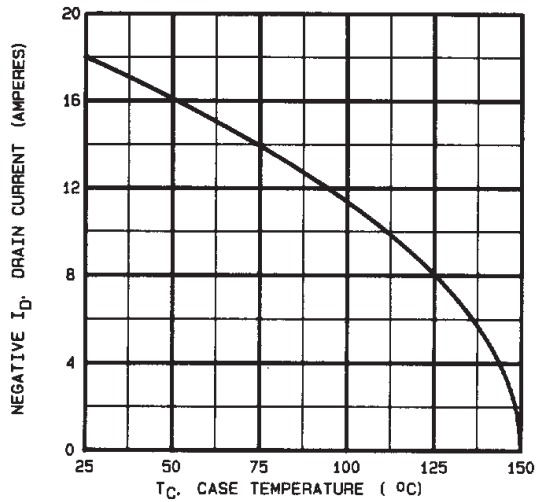


Fig 9. Maximum Drain Current Vs. Case Temperature

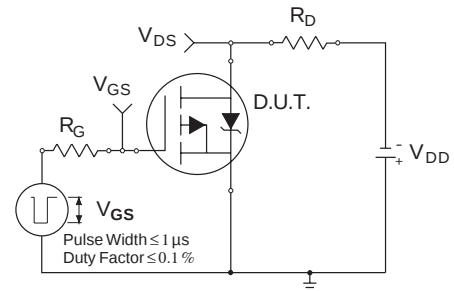


Fig 10a. Switching Time Test Circuit

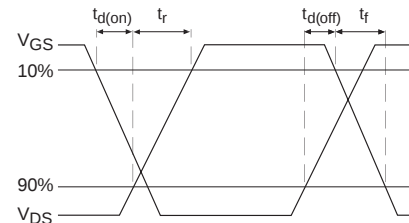


Fig 10b. Switching Time Waveforms

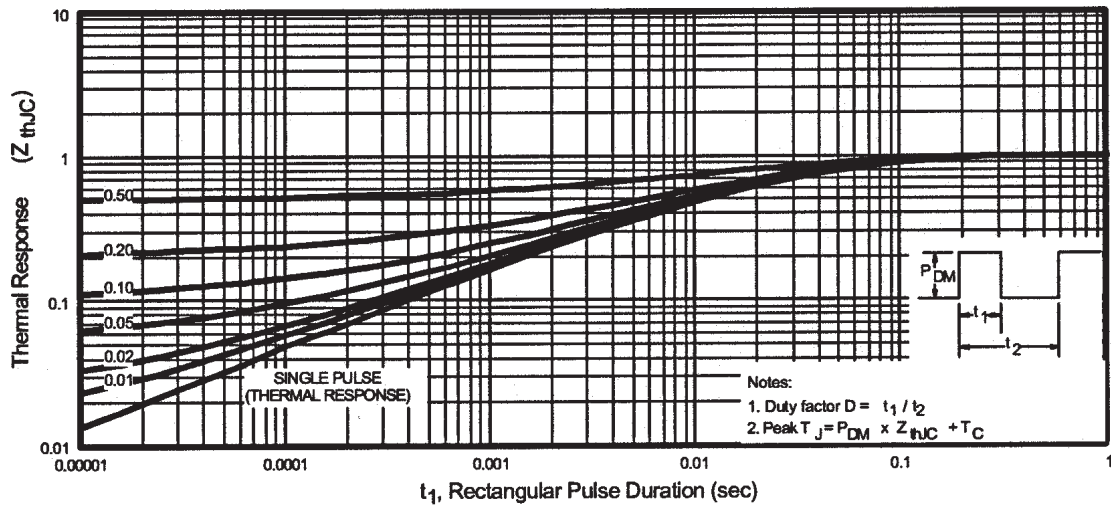


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

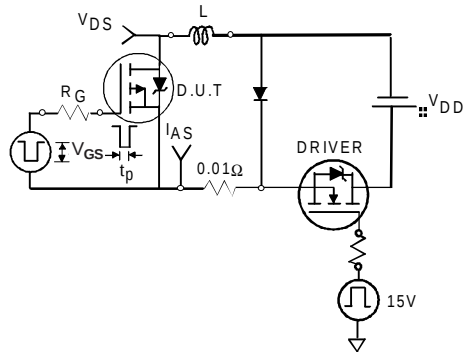


Fig 12a. Unclamped Inductive Test Circuit

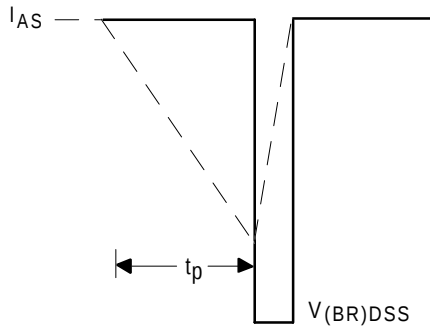


Fig 12b. Unclamped Inductive Waveforms

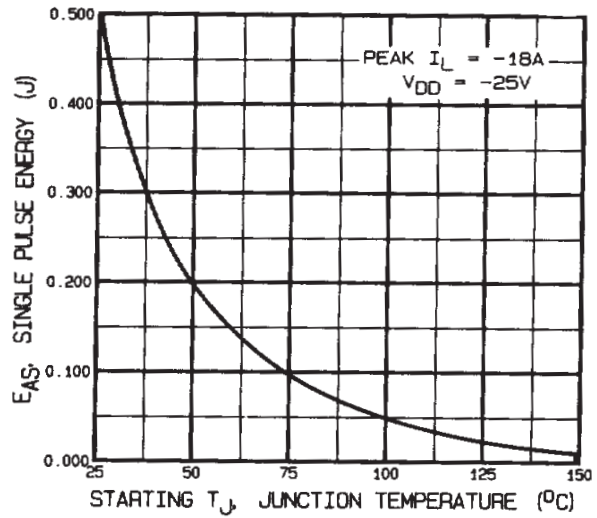


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

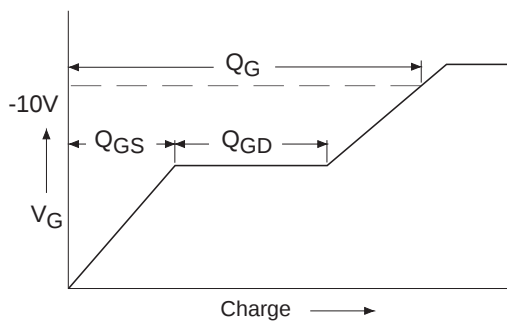


Fig 13a. Basic Gate Charge Waveform

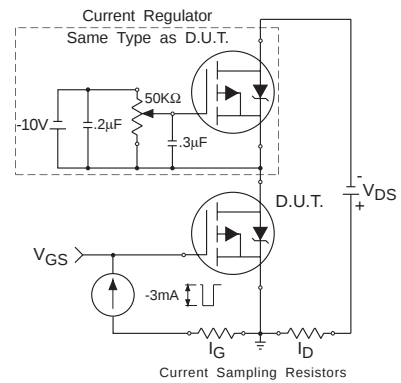


Fig 13b. Gate Charge Test Circuit

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = -25V$, starting $T_J = 25^{\circ}C$, $L = 3.1mH$
Peak $I_L = -18A$, $V_{GS} = -10V$

- ③ $I_{SD} \leq -18A$, $di/dt \leq -100A/\mu s$,
 $V_{DD} \leq -100V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$

[illegible]

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

- 1- DRAIN
- 2- GATE
- 3- SOURCE

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